# Jen-Inn Chyi

List of Publications by Year
in descending order



| 336 | 6,247 | 71102 | 102487 |
|---|---|---|---|
| papers | citations | 41 h-index | 66 g-index |

| 336 | 336 | 336 | 4999 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Performance Comparison of Lattice-Matched AlInN/GaN/AlGaN/GaN Double-Channel Metalâ€“Oxideâ€“Semiconductor High-Electron Mobility Transistors with Planar Channel and Multiple-Mesa-Fin-Channel Array. Materials, 2022, 15, 42. | 2.9 | 1 |
| 2 | AlInGaN/GaN HEMTs With High Johnsonâ€™s Figure-of-Merit on Low Resistivity Silicon Substrate. IEEE Journal of the Electron Devices Society, 2021, 9, 130-136. | 2.1 | 7 |
| 3 | Lattice-Matched AlInN/GaN/AlGaN/GaN Heterostructured-Double-Channel Metal-Oxide-Semiconductor High-Electron Mobility Transistors with Multiple-Mesa-Fin-Channel Array. Materials, 2021, 14, 5474. | 2.9 | 3 |
| 4 | Design and Simulation of High Performance Lattice Matched Double Barrier Normally Off AlInGaN/GaN HEMTs. IEEE Journal of the Electron Devices Society, 2020, 8, 873-878. | 2.1 | 10 |
| 5 | Crystal Transformation of Cubic BN Nanoislands to Rhombohedral BN Sheets on AlN for Deep-UV Light-Emitting Diodes. ACS Applied Nano Materials, 2020, 3, 5285-5290. | 5.0 | 2 |
| 6 | The Influence of Superlattice Structure on the Dynamic Buffer Response of AlInN/GaN-on-Si HEMTs. IEEE Nanotechnology Magazine, 2020, 19, 415-420. | 2.0 | 4 |
| 7 | High Electron Mobility of 1880 cm2 V-S In0.17 Al0.83N/GaN-on-Si HEMTs with GaN Cap Layer. , 2020, , . | | 0 |
| 8 | Enhanced Electrical Properties of AlInN/AlN/GaN Heterostructure using $mathbf{Al}_{mathbf{x}}mathbf{Ga}_{1-mathbf{x}}mathbf{N}/mathbf{Al}_{mathbf{y}}mathbf{Ga}_{1-mathbf{y}}mathbf{N}$ superlattice. , 2019, , . | | 6 |
| 9 | Improved optical properties of InAs submonolayer quantum dots in GaAsSb/InGaAs double-well structure. Applied Physics Letters, 2019, 115, . | 3.3 | 3 |
| 10 | Fabrication of $02.5  mumathrm{m}$ T-Gate AlInGaN/AlN/GaN HEMTs by I-Line Optical Lithography. , 2019, , . | | 0 |
| 11 | Achieving high electron mobility in AlInGaN/GaN heterostructures: The correlation between thermodynamic stability and electron transport properties. Applied Physics Letters, 2019, 114, 222103. | 3.3 | 5 |
| 12 | Design and Demonstration of Tunable Amplified Sensitivity of AlGaN/GaN High Electron Mobility Transistor (HEMT)-Based Biosensors in Human Serum. Analytical Chemistry, 2019, 91, 5953-5960. | 6.5 | 34 |
| 13 | Dynamic monitoring of transmembrane potential changes: a study of ion channels using an electrical double layer-gated FET biosensor. Lab on A Chip, 2018, 18, 1047-1056. | 6.0 | 16 |
| 14 | A Comprehensive Model for Whole Cell Sensing and Transmembrane Potential Measurement Using FET Biosensors. ECS Journal of Solid State Science and Technology, 2018, 7, Q3001-Q3008. | 1.8 | 12 |
| 15 | High sensitivity cardiac troponin I detection in physiological environment using AlGaN/GaN High Electron Mobility Transistor (HEMT) Biosensors. Biosensors and Bioelectronics, 2018, 100, 282-289. | 10.1 | 128 |
| 16 | Enumeration of circulating tumor cells and investigation of cellular responses using aptamer-immobilized AlGaN/GaN high electron mobility transistor sensor array. Sensors and Actuators B: Chemical, 2018, 257, 96-104. | 7.8 | 29 |
| 17 | Beyond the Limit of Ideal Nernst Sensitivity: Ultra-High Sensitivity of Heavy Metal Ion Detection with Ion-Selective High Electron Mobility Transistors. ECS Journal of Solid State Science and Technology, 2018, 7, Q176-Q183. | 1.8 | 11 |
| 18 | High Performance InAlN/GaN/Si High Electron Mobility Transistor Using Microwave Ohmic Annealing Technique. ECS Journal of Solid State Science and Technology, 2018, 7, Q185-Q189. | 1.8 | 1 |

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| 19 | Direct detection of DNA using electrical double layer gated high electron mobility transistor in high ionic strength solution with high sensitivity and specificity. Sensors and Actuators B: Chemical, 2018, 271, 110-117. | 7.8 | 19 |
| 20 | High-field modulated ion-selective field-effect-transistor (FET) sensors with sensitivity higher than the ideal Nernst sensitivity. Scientific Reports, 2018, 8, 8300. | 3.3 | 26 |
| 21 | Effects of GaSb surface preparation on the characteristics of HfO2/Al2O3/GaSb metal-oxide-semiconductor capacitors prepared by atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, . | 2.1 | 5 |
| 22 | Suppressing Ge diffusion by GaAsSb barriers in molecular beam epitaxy of InGaAs on Ge. Physica Status Solidi (B): Basic Research, 2017, 254, 1600589. | 1.5 | 0 |
| 23 | Direct detection of fibrinogen in human plasma using electric-double-layer gated AlGaN/GaN high electron mobility transistors. Applied Physics Letters, 2017, 111, . | 3.3 | 11 |
| 24 | Improved reverse recovery characteristics of inAlN/GaN schottky barrier diode using a SOI substrate. Semiconductor Science and Technology, 2017, 32, 105009. | 2.0 | 2 |
| 25 | Beyond the Debye length in high ionic strength solution: direct protein detection with field-effect transistors (FETs) in human serum. Scientific Reports, 2017, 7, 5256. | 3.3 | 173 |
| 26 | Enhancing the Performance of AlGaN/GaN Schottky Barrier Diodes by SF6Plasma Treatment and Deep Anode Recess. ECS Journal of Solid State Science and Technology, 2017, 6, S3081-S3083. | 1.8 | 3 |
| 27 | InAlN/GaN HEMT using microwave annealing for low temperature ohmic contact formation. , 2017, , . | | 0 |
| 28 | Pt/GaN Schottky Diodes for Highly Sensitive Hydrogen Sulfide Detection. ECS Journal of Solid State Science and Technology, 2016, 5, Q137-Q139. | 1.8 | 4 |
| 29 | Influence of Point Defects on the Properties of Undoped and Ga-Doped ZnO Films Grown by Plasma-Assisted Molecular Beam Epitaxy in an O-Rich Environment. ECS Journal of Solid State Science and Technology, 2016, 5, Q222-Q225. | 1.8 | 10 |
| 30 | Suppressing Ge diffusion by GaAsSb for molecular beam epitaxy of InGaAs on Ge. , 2016, , . | | 0 |
| 31 | Bandgap engineering for normally-off GaAsSb/InGaAs hetero-junction tunneling field-effect transistors with high on-state current. , 2016, , . | | 0 |
| 32 | High Thermal Stability of GaN Schottky Diode with Diamond-Like Carbon (DLC) Anode Design. Journal of the Electrochemical Society, 2016, 163, H155-H158. | 2.9 | 3 |
| 33 | The Characterization of InAlN/AlN/GaN HEMTs Using Silicon-on-Insulator (SOI) Substrate Technology. Journal of the Electrochemical Society, 2016, 163, H110-H114. | 2.9 | 4 |
| 34 | Bottomâ€Up Nanoâ€heteroepitaxy of Waferâ€Scale Semipolar GaN on (001) Si. Advanced Materials, 2015, 27, 4845-4850. | 21.0 | 9 |
| 35 | Reduced Interface States of Atomic-Layer-Deposited Al<sub>2</sub>O<sub>3</sub>/AlGaN/GaN Heterostructure Containing In Situ Grown AlN/GaN Cap Layer and Subjected to Thermal Oxidation. Journal of the Electrochemical Society, 2015, 162, E160-E165. | 2.9 | 1 |
| 36 | Analysis of Threshold Voltage Shift in AlGaN/GaN Heterostructure Field-Effect Transistors with Different Buffer Layers. Journal of the Electrochemical Society, 2015, 162, H522-H526. | 2.9 | 2 |

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| 37 | Low resistivity and low compensation ratio Ga-doped ZnO films grown by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2015, 425, 216-220. | 1.5 | 8 |
| 38 | A Study on the Fiber Dispersion Effect for the Generation of Quasi-Sinusoidal Terahertz Modulations on Optical Pulses. Journal of Lightwave Technology, 2015, 33, 4899-4907. | 4.6 | 2 |
| 39 | Investigations of dynamic performance in AlGaN/GaN HFETs with field plates by stressed Câ€“V and dynamic onâ€resistance measurements. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1099-1103. | 1.8 | 0 |
| 40 | Analysis of the Back-Gate Effect in Normally OFF p-GaN Gate High-Electron Mobility Transistor. IEEE Transactions on Electron Devices, 2015, 62, 507-511. | 3.0 | 23 |
| 41 | Improving the off-state characteristics and dynamic on-resistance of AlInN/AlN/GaN HEMTs with a GaN cap layer. Applied Physics Express, 2015, 8, 064102. | 2.4 | 10 |
| 42 | Device stress evaluation of InAs/AlSb HEMT on silicon substrate with refractory iridium Schottky gate metal. Microelectronic Engineering, 2015, 138, 17-20. | 2.4 | 4 |
| 43 | High hole mobility InGaSb/AlSb QW field effect transistors grown on Si by molecular beam epitaxy. Journal of Crystal Growth, 2015, 425, 385-388. | 1.5 | 4 |
| 44 | The device characteristics of Ir- and Ti-based Schottky gates AlSb/InAs high electron mobility transistors. Microelectronics Reliability, 2015, 55, 890-893. | 1.7 | 1 |
| 45 | Trap-Profile Extraction Using High-Voltage Capacitanceâ€“Voltage Measurement in AlGaN/GaN Heterostructure Field-Effect Transistors With Field Plates. IEEE Transactions on Electron Devices, 2015, 62, 835-839. | 3.0 | 12 |
| 46 | Yellow-emitting Si-doped GaN: Favorable characteristics for intermediate band solar cells. Solar Energy Materials and Solar Cells, 2015, 132, 544-548. | 6.2 | 12 |
| 47 | A Self-Assembled Double-Island Buffer Structure for Improving GaN-Based Materials Grown on Si Substrates. ECS Journal of Solid State Science and Technology, 2014, 3, R229-R233. | 1.8 | 0 |
| 48 | Quantum control study of ultrafast optical responses in semiconductor quantum dot devices. Optics Express, 2014, 22, 30815. | 3.4 | 1 |
| 49 | Passivation of GaSb using molecular beam epitaxy Y2O3 to achieve low interfacial trap density and high-performance self-aligned inversion-channel p-metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2014, 105, . | 3.3 | 31 |
| 50 | Carrier dynamics in dilute II-VI oxide highly mismatched alloys. Proceedings of SPIE, 2014, , . | 0.8 | 0 |
| 51 | Gate leakage current induced trapping in AlGaN/GaN Schottky-gate HFETs and MISHFETs. Nanoscale Research Letters, 2014, 9, 474. | 5.7 | 11 |
| 52 | Investigation of C-terminal domain of SARS nucleocapsid proteinâ€“Duplex DNA interaction using transistors and binding-site models. Sensors and Actuators B: Chemical, 2014, 193, 334-339. | 7.8 | 6 |
| 53 | High Breakdown Voltage and Low Thermal Effect Micromachined AlGaN/GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2014, 14, 726-731. | 2.0 | 8 |
| 54 | Optical and electrical properties of ZnSeO alloys grown by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 180-183. | 1.5 | 11 |

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| 55 | Sb-based semiconductors for low power electronics. Journal of Materials Chemistry C, 2013, 1, 4616. | 5.5 | 21 |
| 56 | High performacne InAs/AlSb HEMT with refractory iridium Schottky gate metal. , 2013, , . | | 0 |
| 57 | AlGaN/GaN high electron mobility transistors for proteinâ€“peptide binding affinity study. Biosensors and Bioelectronics, 2013, 41, 717-722. | 10.1 | 34 |
| 58 | In-Plane Gate Transistors for Photodetector Applications. IEEE Electron Device Letters, 2013, 34, 780-782. | 3.9 | 5 |
| 59 | Identification of the Amount of Binding Sites and Dissociation Constants of a Ligand-Receptor Complex Using AlGaN/GaN High Electron Mobility Transistors. ACS Symposium Series, 2013, , 63-76. | 0.5 | 0 |
| 60 | InGaSb/AlSb pâ€channel HFETs with hydrogen plasma treatment. Electronics Letters, 2013, 49, 499-500. | 1.0 | 1 |
| 61 | Surface Passivation of GaSb(100) Using Molecular Beam Epitaxy of Y<sub>2</sub>O<sub>3</sub>and Atomic Layer Deposition of Al<sub>2</sub>O<sub>3</sub>: A Comparative Study. Applied Physics Express, 2013, 6, 121201. | 2.4 | 13 |
| 62 | Detection of Severe Acute Respiratory Syndrome (SARS) Coronavirus Nucleocapsid Protein Using AlGaN/GaN High Electron Mobility Transistors. ECS Transactions, 2013, 50, 239-243. | 0.5 | 11 |
| 63 | Memory device application of wide-channel in-plane gate transistors with type-II GaAsSb-capped InAs quantum dots. Applied Physics Letters, 2013, 103, 143502. | 3.3 | 9 |
| 64 | Band alignment tuning of InAs quantum dots with a thin AlGaAsSb capping layer. Applied Physics Letters, 2013, 102, . | 3.3 | 7 |
| 65 | Characteristics of InAs/AlSb high electron mobility transistors grown on Si using a GaAsSb step-graded buffer layer. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 061207. | 1.2 | 1 |
| 66 | Efficiency improvement of GaN light emitting diodes on Si by double island growth method. , 2013, , . | | 0 |
| 67 | Human immunodeficiency virus drug development assisted with AlGaN/GaN high electron mobility transistors and binding-site models. Applied Physics Letters, 2013, 102, 173704. | 3.3 | 16 |
| 68 | Growth and Characterization of Crack-Free Semi-Polar (1-101) GaN on 7Â°-off (001) Si Substrates by Metal-Organic Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2013, 2, N3001-N3005. | 1.8 | 5 |
| 69 | Effect of Gate Length on Device Performances of AlSb/InAs High Electron Mobility Transistors Fabricated Using BCl$_{3}$ Dry Etching. Japanese Journal of Applied Physics, 2012, 51, 060202. | 1.5 | 1 |
| 70 | Gate Stack Engineering and Thermal Treatment on Electrical and Interfacial Properties of Ti/Pt/HfO<sub>2</sub>/InAspMOS Capacitors. Active and Passive Electronic Components, 2012, 2012, 1-6. | 0.3 | 1 |
| 71 | Carrier Transport Study of TMIn-Treated InGaN LEDs by Using Quantum Efficiency and Time-Resolved Electro-Luminescence Measurements. Journal of the Electrochemical Society, 2012, 159, H225-H229. | 2.9 | 7 |
| 72 | Characteristic improvements of vertically aligned columnar quantum dot solar cell with a GaAsSb capping layer. , 2012, , . | | 0 |

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| 73 | Investigation of the binding affinity of C-terminal domain of SARS coronavirus nucleocapsid protein to nucleotide using AlGaN/GaN high electron mobility transistors. , 2012, , . | | 1 |
| 74 | Elucidation of dissociation constants and binding sites of antibody-antigen complex using AlGaN/GaN high electron mobility transistors. , 2012, , . | | 0 |
| 75 | Temperature-dependent decay dynamics in highly mismatched ZnSe1â^'‹i›x‹/i›Te‹i›x‹/i› alloy. Applied Physics Letters, 2012, 100, . | 3.3 | 4 |
| 76 | Device Characteristics of InGaSb/AlSb High-Hole-Mobility FETs. IEEE Electron Device Letters, 2012, 33, 964-966. | 3.9 | 11 |
| 77 | Improving the characteristics of intermediate-band solar cell devices using a vertically aligned InAs/GaAsSb quantum dot structure. Solar Energy Materials and Solar Cells, 2012, 105, 237-241. | 6.2 | 51 |
| 78 | A gold-free fully copper metalized AlGaN/GaN power HEMTs on Si substrate. Microelectronics Reliability, 2012, 52, 2556-2560. | 1.7 | 3 |
| 79 | Photomodulation reflectance study of temperature dependence of the band gap of ZnSe‹sub›1â€‹‹i›x‹/i›‹/sub›O‹i›‹sub›x‹/sub›‹/i›. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 187-189. | 0.8 | 6 |
| 80 | A 600 V AlGaN/GaN Schottky barrier diode on silicon substrate with fast reverse recovery time. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 949-952. | 0.8 | 16 |
| 81 | Broadband terahertz ultrasonic transducer based on a laser-driven piezoelectric semiconductor superlattice. Ultrasonics, 2012, 52, 1-4. | 3.9 | 26 |
| 82 | Propagation, Resonance, and Radiation on Terahertz Optoelectronic Integrated Circuits. IEEE Photonics Journal, 2012, 4, 699-706. | 2.0 | 3 |
| 83 | Efficiency Enhancement of InGaN LEDs With an n-Type AlGaN/GaN/InGaN Current Spreading Layer. IEEE Electron Device Letters, 2011, 32, 1409-1411. | 3.9 | 17 |
| 84 | High-Performance AlGaN/GaN Schottky Diodes With an AlGaN/AlN Buffer Layer. IEEE Electron Device Letters, 2011, 32, 1519-1521. | 3.9 | 51 |
| 85 | Effects of GaAsSb capping layer thickness on the optical properties of InAs quantum dots. Applied Physics Letters, 2011, 99, 073108. | 3.3 | 31 |
| 86 | Growth of crack-free semi-polar (1-101) GaN on a 7Â°-off (001) Si substrate by metal-organic chemical vapor deposition. , 2011, , . | | 1 |
| 87 | Electrical properties of In-doped ZnO films grown by plasma-assisted molecular beam epitaxy on GaN(0001) template. Proceedings of SPIE, 2011, , . | 0.8 | 0 |
| 88 | Optical properties of InGaN/GaN multiple quantum wells with trimethylindium treatment during growth interruption. Journal of Crystal Growth, 2011, 325, 41-45. | 1.5 | 8 |
| 89 | High optical property vertically aligned InAs quantum dot structures with GaAsSb overgrown layers. Journal of Crystal Growth, 2011, 323, 164-166. | 1.5 | 18 |
| 90 | The impact of trimethylindium treatment time during growth interruption on the carrier dynamics of InGaN/GaN multiple quantum wells. Thin Solid Films, 2011, 519, 6092-6096. | 1.8 | 12 |

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| 91 | Terahertz photonic transmitters with a high-gain open-ended rampart slot array antenna. , 2010, , . | | 1 |
| 92 | DC Characteristics of InAlAs/InGaAsSb/InGaAs Double Heterojunction Bipolar Transistors. IEEE Transactions on Electron Devices, 2010, 57, 3327-3332. | 3.0 | 4 |
| 93 | Challenges and Opportunities in GaN and ZnO Devices and Materials [Scanning the Issue]. Proceedings of the IEEE, 2010, 98, 1113-1117. | 21.3 | 8 |
| 94 | Characterization and Comparison of GaAs/AlGaAs Uni-Traveling Carrier and Separated-Transport-Recombination Photodiode Based High-Power Sub-THz Photonic Transmitters. IEEE Journal of Quantum Electronics, 2010, 46, 19-27. | 1.9 | 9 |
| 95 | Extremely High Saturation Current-Bandwidth Product Performance of a Near-Ballistic Uni-Traveling-Carrier Photodiode With a Flip-Chip Bonding Structure. IEEE Journal of Quantum Electronics, 2010, 46, 80-86. | 1.9 | 64 |
| 96 | Tailoring of the Wave Function Overlaps and the Carrier Lifetimes in InAs/GaAs1â^'xSbx Type-II Quantum Dots. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2524-2528. | 2.7 | 4 |
| 97 | Fabrication study of AlN solarâ€blind (<280â€‰nm) MSM photodetectors grown by lowâ€temperature deposition. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 224-228. | 1.8 | 12 |
| 98 | Temperature-Dependent Characteristics of a GaN/InGaN/ZnO Heterojunction Bipolar Transistor. Journal of the Electrochemical Society, 2010, 157, H381. | 2.9 | 8 |
| 99 | N<sup>+</sup>-InGaAs/InAlAs recessed gates for InAs/AlSb HFET development. , 2010, , . | | 0 |
| 100 | Spectroscopic ellipsometric analysis of ZnSe1â^'xOx layers with different O compositions. Journal of Applied Physics, 2010, 108, . | 2.5 | 2 |
| 101 | Photoluminescence of self-assembled InAs quantum dots embedded in photonic crystal nanocavities with shifted air holes. Nanotechnology, 2010, 21, 055201. | 2.6 | 1 |
| 102 | Site-controlled self-assembled InAs quantum dots grown on GaAs substrates. Nanotechnology, 2010, 21, 295304. | 2.6 | 4 |
| 103 | Effects of Lens Shape on GaN Grown on Microlens Patterned Sapphire Substrates by Metallorganic Chemical Vapor Deposition. Journal of the Electrochemical Society, 2010, 157, H304. | 2.9 | 30 |
| 104 | Low Surface Recombination in InAlAs/InGaAsSb/InGaAs Double Heterojunction Bipolar Transistors. IEEE Electron Device Letters, 2010, 31, 1401-1403. | 3.9 | 4 |
| 105 | Room-temperature operation type-II GaSb/GaAs quantum-dot infrared light-emitting diode. Applied Physics Letters, 2010, 96, . | 3.3 | 55 |
| 106 | Room-temperature operation type-II GaSb/GaAs quantum-dot infrared light-emitting diode. , 2010, , . | | 1 |
| 107 | Ti- and Pt-based Schottky gates for InGaSb p-channel HFET development. , 2010, , . | | 0 |
| 108 | DC and RF characteristics of InAs-channel MOS-MODFETs using PECVD SiO<inf>2</inf> as gate dielectrics. , 2010, , . | | 0 |

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| 109 | Characterization of InAlAs/In<inf>0.25</inf>Ga<inf>0.75</inf>As<inf>0.72</inf>Sb<inf>0.28</inf>/InGaAs double heterojunction bipolar transistors. , 2010, , . | | |
| 110 | Origins of nonzero multiple photon emission probability from single quantum dots embedded in photonic crystal nanocavities. Applied Physics Letters, 2009, 94, 163111. | 3.3 | 3 |
| 111 | Photogeneration of coherent shear phonons in orientated wurtzite semiconductors by piezoelectric coupling. Physical Review B, 2009, 80, . | 3.2 | 29 |
| 112 | Effects of thermal annealing on the emission properties of type-II InAs/GaAsSb quantum dots. Applied Physics Letters, 2009, 94, 053101. | 3.3 | 40 |
| 113 | Electrically manipulating the optical sensitivity function in quantum wells for nanoacoustic wave detection. Applied Physics Letters, 2009, 95, 143108. | 3.3 | 2 |
| 114 | InAlAs/InGaAsSb/InGaAs double heterojunction bipolar transistors with high current gain and low base sheet resistance. , 2009, , . | | 0 |
| 115 | Proton irradiation effects on Sb-based heterojunction bipolar transistors. Journal of Vacuum Science & Technology B, 2009, 27, L33. | 1.3 | 1 |
| 116 | The Structure of GaN-Based Transverse Junction Blue LED Array for Uniform Distribution of Injected Current/Carriers. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1292-1297. | 2.9 | 11 |
| 117 | Exciton fine structures and energy transfer in single InGaAs quantumâ€dot molecules. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 860-863. | 0.8 | 1 |
| 118 | Timeâ€resolved photoluminescence of typeâ€II InAs/GaAs quantum dots covered by a thin GaAs<sub>1â€“x</sub>Sb<sub>x</sub> layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1449-1452. | 0.8 | 5 |
| 119 | Investigations of photo-assisted conductive atomic force microscopy on III-nitrides. Microelectronics Journal, 2009, 40, 353-356. | 2.0 | 1 |
| 120 | The Monolithic Integration of GaAsâ€“AlGaAs-Based Unitraveling-Carrier Photodiodes With Zn-Diffusion Vertical-Cavity Surface-Emitting Lasers With Extremely High Data Rate/Power Consumption Ratios. IEEE Photonics Technology Letters, 2009, 21, 1444-1446. | 2.5 | 6 |
| 121 | Metal-oxide-HEMT on 6.1Å antimonides. , 2009, , . | | 1 |
| 122 | An electrically driven quasi-L2 photonic crystal nano-cavity with a small mode volume. , 2009, , . | | 0 |
| 123 | Low-leakage InAS/AlSb HEMT with high FT-LG product. , 2009, , . | | 2 |
| 124 | Low-resistance smooth-surface Ti/Al/Cr/Mo/Au n-type Ohmic contact to AlGaN/GaN heterostructures. Applied Physics Letters, 2009, 94, . | 3.3 | 19 |
| 125 | Improved surface morphology and edge definition for ohmic contacts to AlGaN/GaN heterostructures. Proceedings of SPIE, 2009, , . | 0.8 | 2 |
| 126 | Growth of high quality AlN on sapphire by using a low-temperature AlN interlayer. , 2009, , . | | 3 |

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| 127 | Polarization-Enhanced Mg Doping in InGaN/GaN Superlattice for Green Light-Emitting Diodes. , 2009, , . | | 3 |
| 128 | Bias-Controlled Coherent Acoustic Phonon Generation in InGaN/GaN Multiple-Quantum-Wells Light Emitting Diodes. , 2009, , . | | 0 |
| 129 | Luminescence mechanism and carrier dynamic studies of InGaN-based dichromatic light emitting diodes with ultraviolet and blue emissions. Thin Solid Films, 2008, 517, 909-915. | 1.8 | 9 |
| 130 | Site-controlled InGaAs quantum dots grown on a GaAs multi-faceted microstructure for single photon emissions. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2713-2715. | 0.8 | 3 |
| 131 | Highly Directed Radiation Pattern From a THz Photonic Transmitter With a Two-Dimensional Rampart Slot Array Antenna. IEEE Photonics Technology Letters, 2008, 20, 1042-1044. | 2.5 | 1 |
| 132 | Enhanced Normal-Incident Absorption of Quantum-Dot Infrared Photodetectors With Smaller Quantum Dots. IEEE Photonics Technology Letters, 2008, 20, 1240-1242. | 2.5 | 9 |
| 133 | Light Output Enhancement of InGaN Light-Emitting Diodes Grown on Masklessly Etched Sapphire Substrates. IEEE Photonics Technology Letters, 2008, 20, 1621-1623. | 2.5 | 27 |
| 134 | Ultra low turn-on voltage and high-current InP DHBT with a pseudomorphic In<inf>0.37</inf>Ga<inf>0.63</inf>As<inf>0.89</inf>Sb<inf>0.11</inf> base. , 2008, , . | | 0 |
| 135 | High extractive single-photon emissions from InGaAs quantum dots on a GaAs pyramid-like multifaceted structure. Nanotechnology, 2008, 19, 045714. | 2.6 | 6 |
| 136 | Growth and characterization of crack-free semipolar {1-101}InGaNâˆ•GaN multiple-quantum well on V-grooved (001)Si substrates. Applied Physics Letters, 2008, 92, . | 3.3 | 17 |
| 137 | Low Turn-On Voltage and High-Current $hbox{InP}/hbox{In}_{0.37}hbox{Ga}_{0.63}hbox{As}_{0.89}hbox{Sb}_{0.11}/hbox{In}_{0.53}hbox{Ga}_{0.47}hbox{As}$ Double Heterojunction Bipolar Transistors. IEEE Electron Device Letters, 2008, 29, 655-657. | 3.9 | 17 |
| 138 | Nonresonant carrier transfer in single InGaAs/GaAs quantum dot molecules. Physical Review B, 2008, 77, . | 3.2 | 14 |
| 139 | Carrier dynamics of type-II InAsâˆ•GaAs quantum dots covered by a thin GaAs1âˆ’xSbx layer. Applied Physics Letters, 2008, 93, . | 3.3 | 41 |
| 140 | Enhancing the quantum efficiency of InGaN green light-emitting diodes by trimethylindium treatment. Applied Physics Letters, 2008, 92, 161113. | 3.3 | 25 |
| 141 | DC and RF characteristics of type II lineup InAs/AlSb HFETs. , 2008, , . | | 0 |
| 142 | Highly-directed terahertz photonic transmitter by using the design of planar antenna arrays. , 2008, , . | | 0 |
| 143 | Enhancing the light extraction of InGaN light-emitting diodes by patterning the dicing streets. , 2008, , . | | 0 |
| 144 | Epitaxial lateral overgrowth of GaN on AlGaN/(111)Si micropillar array fabricated by polystyrene microsphere lithography. , 2008, , . | | 2 |

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| 145 | Emission Intensity Improvement of InGaN Ultraviolet Light-Emitting Diodes Grown on Wet-Etched Sapphire Substrates. , 2007, , . | | 0 |
| 146 | Single photon emission from an InGaAs quantum dot precisely positioned on a nanoplane. Applied Physics Letters, 2007, 90, 073105. | 3.3 | 27 |
| 147 | Crack-free GaN grown on AlGaNâˆ•(111)Si micropillar array fabricated by polystyrene microsphere lithography. Applied Physics Letters, 2007, 91, 261910. | 3.3 | 13 |
| 148 | DC Characteristics of GaAsSb/InGaAs Type-II Heterojunction Bipolar Transistor. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , . | 0.0 | 0 |
| 149 | Light output improvement of InGaN ultraviolet light-emitting diodes by using wet-etched stripe-patterned sapphire substrates. Journal of Applied Physics, 2007, 102, 084503. | 2.5 | 35 |
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